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CGD1042L

1 GHz, 23 dB gain GaAs low current power doubler

Rev. 1 — 10 March 2014

Product data sheet

1. Product profile

1.1 General description

Hybrid amplifier module in a SOT115AE package, operating at a supply voltage of 24 V Direct Current (DC), employing Heterojunction Field Effect Transistor (HFET) GaAs dies.

1.2 Features and benefits

- Low power consumption
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Adjustable supply current
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

CATV systems operating in the 40 MHz to 1 GHz frequency range.

1.4 Quick reference data

Table 1. Quick reference data

Bandwidth 40 MHz to 1006 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		20.5	21.5	22.5	dB
		f = 1006 MHz		22	23	24	dB
СТВ	composite triple beat	$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	2]	-	-61	-56	dBc
CSO	composite second-order distortion	$V_0 = 51 \text{ dBmV at } 550 \text{ MHz}$	2]	-	-68	-64	dBc
I _{tot}	total current	pin 4 not connected	3]	355	375	395	mΑ
		pin 4 connected to ground	3]	-	330	-	mΑ

^{[1] 77} NTSC; [f = 54 MHz to 550 MHz]; flat V_0 till 550 MHz.



^[2] pin 4 not connected.

^[3] Direct Current (DC).

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input		6
2, 3	common	1 5 7 9	1 4 5 9
4	I _{CC} adjust [1]		
5	+V _B		2 3 7 8
7, 8	common		aaa-011041
9	output		

^[1] The total supply current can be adjusted by pin 4. Grounding of pin 4 gives the lowest supply current while floating of pin 4 gives the maximum supply current.

3. Ordering information

Table 3. Ordering information

Type number	Packag	je	
	Name	Description	Version
CGD1042L	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 × 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads	SOT115AE

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_B	supply voltage		-	30	٧
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
l _l	input current	on I _{CC} adjust (pin 4)	-10	0	mA
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

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5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1006 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		20.5	21.5	22.5	dB
		f = 1006 MHz		22	23	24	dB
SL _{sl}	slope straight line	f = 40 MHz to 1006 MHz	<u>[1]</u>	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1006 MHz	[2]	-	-	0.8	dB
RLin	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		16	-	-	dB
		f = 870 MHz to 1006 MHz		14	-	-	dB
RLout	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1006 MHz		16	-	-	dB
NF	noise figure	f = 50 MHz		-	5.2	6.0	dB
		f = 1006 MHz		-	5.7	6.5	dB
Pin 4 no	connected						
I _{tot}	total current		[3]	355	375	395	mA
77 NTSC	channels						
СТВ	composite triple beat	V _o = 51 dBmV at 550 MHz	[4]	-	-61	-56	dBc
CSO	composite second-order distortion	V _o = 51 dBmV at 550 MHz	[4]	-	-68	-64	dBc
		V _o = 51 dBmV at 550 MHz	[4][8]	-	-71	-67	dBc
Xmod	cross modulation	V _o = 51 dBmV at 550 MHz	[4][5]	-	-60	-	dB
79 NTSC	channels + 75 digital channels						
СТВ	composite triple beat	V _o = 54 dBmV at 1006 MHz	[6]	-	-75	-	dBc
CSO	composite second-order distortion	V _o = 54 dBmV at 1006 MHz	[6]	-	-77	-	dBc
Xmod	cross modulation	V _o = 54 dBmV at 1006 MHz	[5][6]	-	-68	-	dB
CCN	carrier-to-composite noise	V _o = 54 dBmV at 1006 MHz	<u>[6]</u>	-	62	-	dBc
74 NTSC	channels + 36 digital channels			,	,		-
СТВ	composite triple beat	V _o = 51 dBmV at 770 MHz	[7]	-	-65	-	dBc
CSO	composite second-order distortion	V _o = 51 dBmV at 770 MHz	[7]	-	-73	-	dBc
Xmod	cross modulation	V _o = 51 dBmV at 770 MHz	[5][7]	-	-54	-	dB

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 Table 5.
 Characteristics ...continued

Bandwidth 40 MHz to 1006 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Pin 4 con	nected to ground	,					
I _{tot}	total current		[3]	-	330	-	mA
77 NTSC	channels				'		
СТВ	composite triple beat	V _o = 51 dBmV at 550 MHz	[4]	-	-53	-	dBc
CSO	composite second-order distortion	V _o = 51 dBmV at 550 MHz	[4]	-	-68	-	dBc
79 NTSC	channels + 75 digital channels				'		
СТВ	composite triple beat	V _o = 54 dBmV at 1006 MHz	[6]	-	-66	-	dBc
CSO	composite second-order distortion	V _o = 54 dBmV at 1006 MHz	[6]	-	-77	-	dBc
CCN	carrier-to-composite noise	V _o = 54 dBmV at 1006 MHz	[6]	-	59	-	dBc
74 NTSC	channels + 36 digital channels				•		
СТВ	composite triple beat	V _o = 51 dBmV at 770 MHz	[7]	-	-59	-	dBc
CSO	composite second-order distortion	V _o = 51 dBmV at 770 MHz	[7]	-	-73	-	dBc

- [1] G_p at 1003 MHz minus G_p at 40 MHz.
- [2] Flatness is defined as peak deviation to straight line.
- [3] Direct Current (DC).
- [4] 77 NTSC; [f = 54 MHz to 550 MHz]; flat V_0 till 550 MHz.
- [5] Measured at 55.25 MHz.
- [6] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1006 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1006 MHz.
- [7] 74 NTSC channels [f = 70 MHz to 550 MHz] + 36 digital channels [f = 550 MHz to 770 MHz] (-10 dB offset); tilt = 0 dB.
- [8] Measured at 78 MHz.

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads

SOT115AE

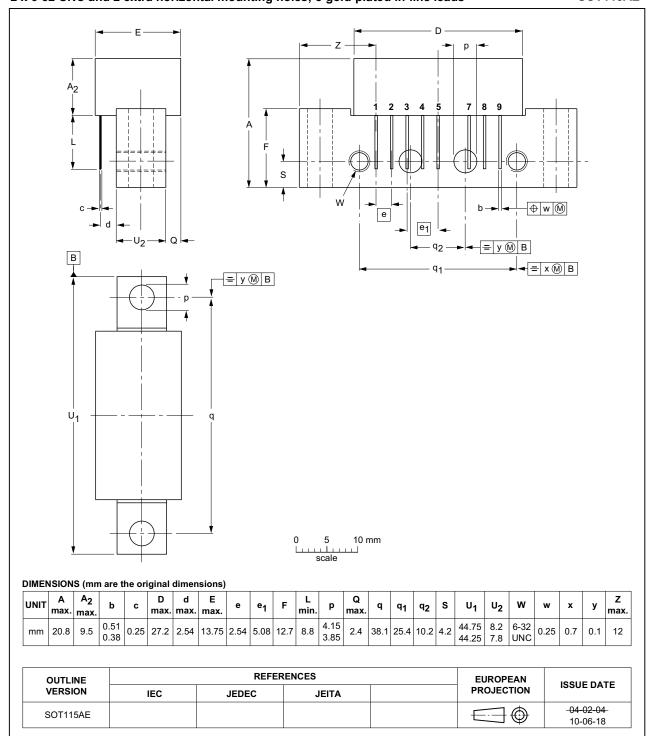


Fig 1. Package outline SOT115AE

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7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1042L v.1	20140310	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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